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NTE398 Silicon PNP Transistor TV Vertical Output (Compl to NTE375)

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	200V
Collector–Emitter Voltage, V_{CEO}	150V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	2A
Pulsed (Note 1)	3A
Collector Dissipation ($T_C = +25^\circ\text{C}$), P_C	25W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Note 1. Pulse Width \leq 10ms, Duty Cycle \leq 50%.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 150V, I_E = 0$	–	–	50	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$	–	–	50	μA
DC Current Gain	h_{FE}	$V_{CE} = 10V, I_C = 400\text{mA}$, Note 2	60	–	120	
Gain Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 400\text{mA}$, Note 2	–	5	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	–	–	1.0	V

Note 2. Pulse Width \leq 350 μs , Duty Cycle \leq 25%/Pulsed.

